

**Department of Electrical Engineering
Indian Institute of Technology, Kanpur**

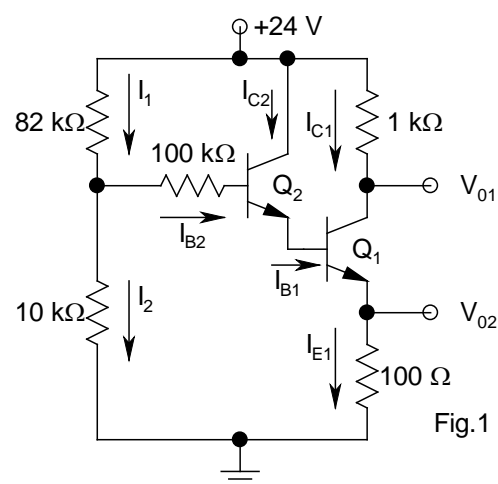
EE 210

Assignment #5

Assigned: 5.2.25

1. Consider the 4-resistor bias network for BJTs, as discussed in class. Assume $V_{CC} = 12\text{ V}$, $\beta = 100$, $R_C = 4\text{ k}\Omega$, $R_E = 4\text{ k}\Omega$, and the current through R_1 is 20 times the base current of the transistor.
 - a) Using the simple analysis given in class, choose the required values of R_1 and R_2 such that the DC collector current is 1 mA. What is the value of V_{CE} ?
 - b) Now, using the values of R_1 and R_2 chosen in part a), perform an exact analysis of the circuit, and determine the actual values of I_C and V_{CE} . How do they compare with the results of part a)?

2. For the circuit shown in Fig.1, transistors Q_1 ($\beta_1 = 100$) and Q_2 ($\beta_2 = 50$) are operating in the forward active region. Find all the currents marked in the figure. Calculate V_{01} and V_{02} . Hence, determine V_{CE1} and V_{CE2} . Comment on the biasing.



3. Consider the four resistor bias network for MOSFETs, as discussed in class. Assume $V_{DD} = 5\text{ V}$, $R_S = 8\text{ k}\Omega$, and the body is tied to $V_B = -1\text{ V}$. The required DC quiescent drain current $I_{DQ} = 200\text{ }\mu\text{A}$, the DC quiescent power dissipation should not exceed 2 mW, and the circuit should be under the best biasing. Determine the required values of R_1 , R_2 , and R_D . Data: $V_{TN0} = 1\text{ V}$, $(W/L) = 10$, $k'_N = 40\text{ }\mu\text{A/V}^2$, $\gamma = 0.4\text{ V}^{1/2}$, and $2\phi_F = 0.6\text{ V}$. Neglect the CLM effect.
4. Perform a self-consistent analysis (i.e., without assuming that $V_{BE} = 0.7\text{ V}$) of the simple BJT current mirror discussed in class, and determine the reference current I_{REF} and the output current I_0 , neglecting the base width modulation effect, and assuming $V_{CC} = 5\text{ V}$ and $R = 4.3\text{ k}\Omega$. Assume that the transistor saturation currents $I_{S1} = I_{S2} = 10^{-16}\text{ A}$, and the current gains $\beta_1 = \beta_2 = 50$. Now, assuming that the Early voltage V_{A2} of transistor Q_2 is 100 V, determine I_0 and the corresponding value of the output resistance R_0 of the mirror.
5. Design (i.e., calculate the required values of the aspect ratios of the two transistors) a simple MOSFET current mirror discussed in class, and find the value of the resistor R , such that the output current is at least $50\text{ }\mu\text{A}$ for V_0 as low as 0.1 V , and the current in the reference branch is $100\text{ }\mu\text{A}$: i) neglecting body effect, and ii) assuming that the bodies of M_1 and M_2 are connected to -1 V and -2 V respectively. Comment on the answers. Assume $V_{DD} = 5\text{ V}$, the transistors are otherwise matched with $k'_N = 40\text{ }\mu\text{A/V}^2$, $\gamma = 0.4\text{ V}^{1/2}$, $2\phi_F = 0.6\text{ V}$, and $V_{TN0} = 0.7\text{ V}$. For both parts, neglect the CLM effect.